

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,060,599 B2
APPLICATION NO. : 10/804578
DATED : June 13, 2006
INVENTOR(S) : Fernando Gonzalez and Randhir Thakur

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On the title page:

In the section (56) References Cited:
OTHER PUBLICATIONS

delete second occurrence of "Shu Qin, et al., "Plasma Immersion Ion Implantation Doping Experiments for Microelectronics," pp. 962-968, J. Vac. Sci. Technol. B 12(2), Mar./Apr. 1994."

In the specification:

COLUMN 2, Line 42,

change "modern integrated circuit" to
--modern integrated circuit--

COLUMN 6, Line 32,

after "portion" insert --28--

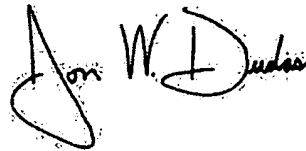
In the claims:

CLAIM 3, COLUMN 8, LINE 21,

change "1750 Åfrom" to --1750 Å from--

Signed and Sealed this

Second Day of January, 2007



JON W. DUDAS
Director of the United States Patent and Trademark Office